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# FDV305N

# 20V N-Channel PowerTrench® MOSFET

## **General Description**

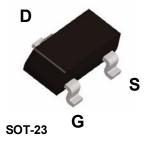
This 20V N-Channel MOSFET uses Fairchild's high voltage PowerTrench process. It has been optimized for power management applications.

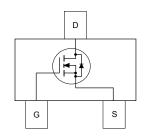
### **Applications**

- Load switch
- Battery protection
- Power management

### **Features**

- 0.9 A, 20 V  $R_{DS(ON)}$  = 220  $m\Omega$  @  $V_{GS}$  = 4.5 V  $R_{DS(ON)}$  = 300  $m\Omega$  @  $V_{GS}$  = 2.5 V
- Low gate charge
- · Fast switching speed
- High performance trench technology for extremely low R<sub>DS(ON)</sub>





Absolute Maximum Ratings T<sub>A</sub>=25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V <sub>DSS</sub>	Drain-Source Voltage	20	V
V <sub>GSS</sub>	Gate-Source Voltage	± 12	V
I <sub>D</sub>	Drain Current - Continuous	0.9	Α
	– Pulsed	2	
P <sub>D</sub>	Maximum Power Dissipation	0.35	W
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range -55 to +150		°C

## **Thermal Characteristics**

 $R_{\theta JA}$  Thermal Resistance, Junction-to-Ambient 357 °C/W

**Package Marking and Ordering Information** 

Device Marking		Device	Reel Size	Tape width	Quantity
	305	FDV305N	7"	8mm	3000 units

Symbol	Parameter	Test C	onditions	Min	Тур	Max	Units
Off Char	acteristics						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0 V,	I <sub>D</sub> = 250 μA	20			V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA,Re	eferenced to 25°C		15		mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 16 V,	V <sub>GS</sub> = 0 V			1	μА
I <sub>GSSF</sub>	Gate–Body Leakage, Forward	V <sub>GS</sub> = 12 V,	$V_{DS} = 0 V$			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage, Reverse	$V_{GS} = -12 V$ ,	V <sub>DS</sub> = 0 V			-100	nA
On Char	acteristics (Note 2)						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$	I <sub>D</sub> = 250 μA	0.6	1	1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA,Re	eferenced to 25°C		-3		mV/°C
$R_{DS(on)}$	Static Drain–Source On–Resistance	$V_{GS} = 4.5 \text{ V},$ $V_{GS} = 2.5 \text{ V},$ $V_{GS} = 4.5 \text{V}, I_D = 4.5 \text{V},$	$I_D = 0.9 \text{ A}$ $I_D = 0.7 \text{ A}$ $= 0.9 \text{ A}, T_J = 125^{\circ}\text{C}$		164 235 220	220 300 303	mΩ
I <sub>D(on)</sub>	On-State Drain Current	$V_{GS} = 4.5V$ ,		1			Α
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 5V,	I <sub>D</sub> = 0.9 A		3		S
Dvnamio	Characteristics						
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 10 V,	V <sub>GS</sub> = 0 V,		109		pF
Coss	Output Capacitance	f = 1.0 MHz		30		pF	
$C_{\text{rss}}$	Reverse Transfer Capacitance		1		14		pF
Switchir	g Characteristics (Note 2)						
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 10 V,	I <sub>D</sub> = 1 A,		4.5	9	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{GS} = 4.5 V,$	$R_{GEN}$ = 6 $\Omega$		7	14	ns
t <sub>d(off)</sub>	Turn-Off Delay Time				8	16	ns
t <sub>f</sub>	Turn-Off Fall Time				1.4	2.8	ns
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> = 10 V,	I <sub>D</sub> = 0.9 A,		1.1	1.5	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = 4.5 V			0.26		nC
$Q_{gd}$	Gate-Drain Charge				0.26		nC
Drain-S	ource Diode Characteristics	and Maximur	m Ratings				
I <sub>S</sub>	Maximum Continuous Drain–Source					0.29	Α
V <sub>SD</sub>	Drain–Source Diode Forward Voltage	V <sub>GS</sub> = 0 V,			0.75	1.2	V
t <sub>rr</sub>	Diode Reverse Recovery Time	I <sub>F</sub> = 0.9 A.			7.4		nS
чr	Blodd Hoverdo Hood vory Time	., 0.0.,					

#### Notes:

<sup>1.</sup> Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%

# **Typical Characteristics**

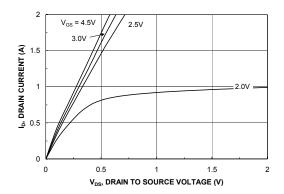


Figure 1. On-Region Characteristics.

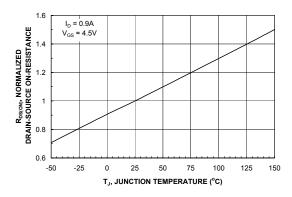


Figure 3. On-Resistance Variation with Temperature.

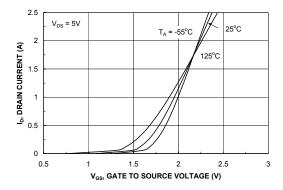


Figure 5. Transfer Characteristics.

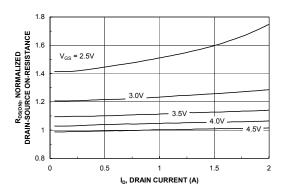


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

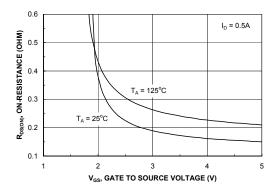


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

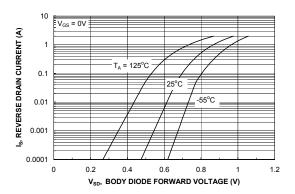
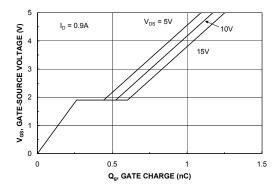


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

# **Typical Characteristics**



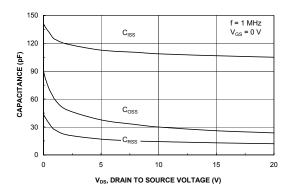
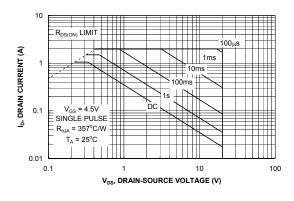


Figure 7. Gate Charge Characteristics.





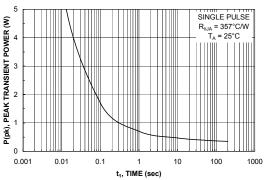


Figure 9. Maximum Safe Operating Area.



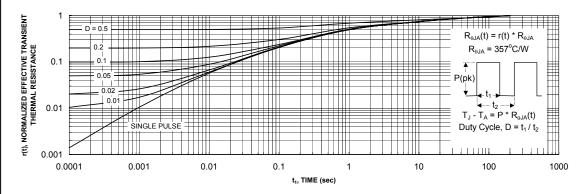


Figure 11. Transient Thermal Response Curve.

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